

[illegible]

A cross-sectional view of a semiconductor device. A substrate 10 is shown with a trench 13. A gate structure 16 is formed on the trench 13. The gate structure 16 includes a gate oxide layer 14 and a gate electrode 15. The gate electrode 15 is connected to a power supply 18. The gate oxide layer 14 is connected to a ground 17. The gate structure 16 is formed on the trench 13. The gate oxide layer 14 is formed on the trench 13. The gate electrode 15 is formed on the gate oxide layer 14. The gate electrode 15 is connected to a power supply 18. The gate oxide layer 14 is connected to a ground 17. The gate structure 16 is formed on the trench 13. The gate oxide layer 14 is formed on the trench 13. The gate electrode 15 is formed on the gate oxide layer 14. The gate electrode 15 is connected to a power supply 18. The gate oxide layer 14 is connected to a ground 17.

APPROVED	O.G. FIG.	
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Fig. 7

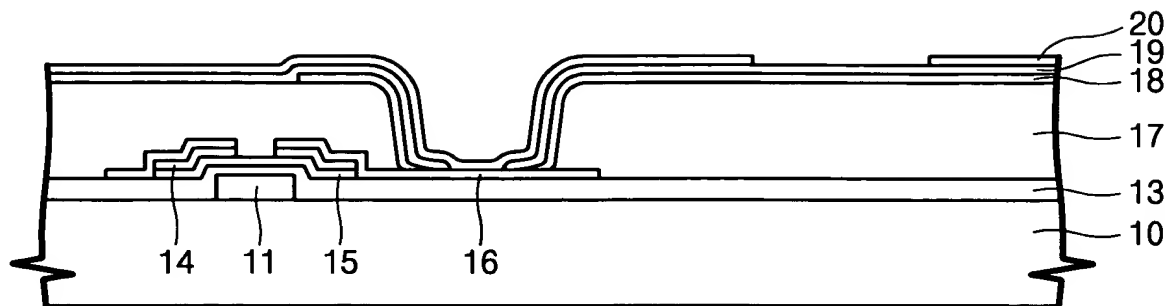


Fig. 8

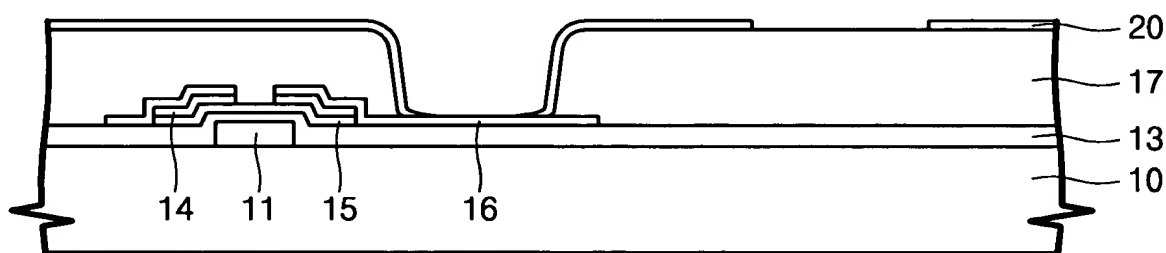


Fig. 9

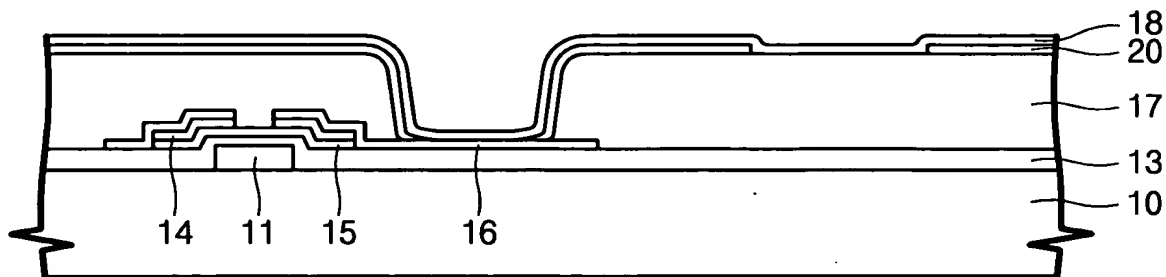


Fig. 10

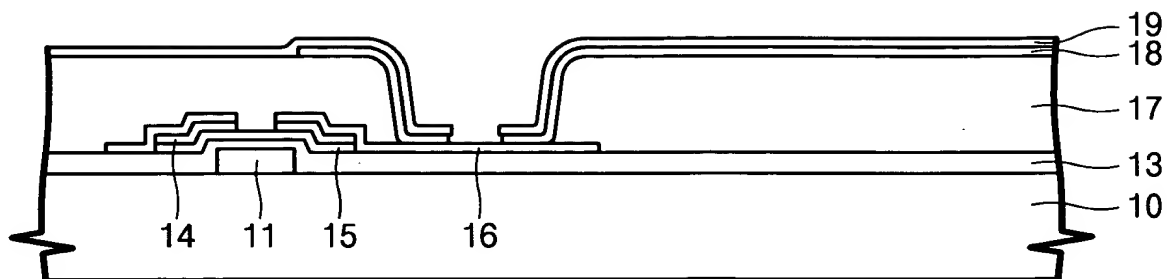


Fig. 11

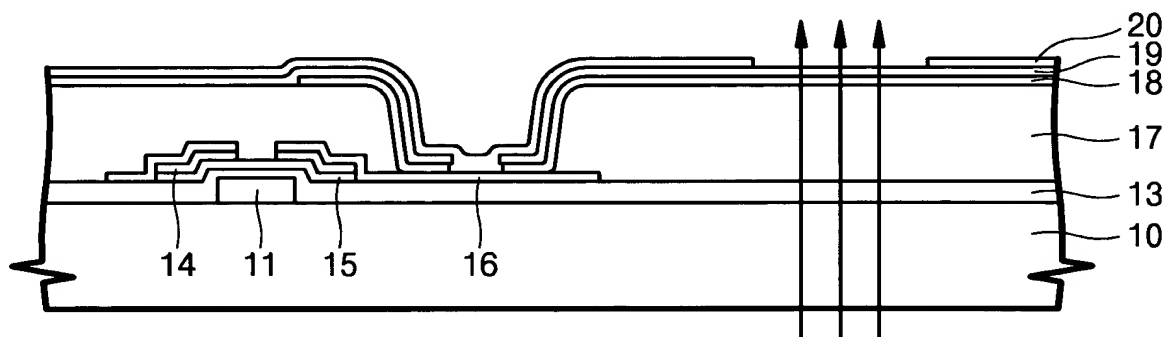
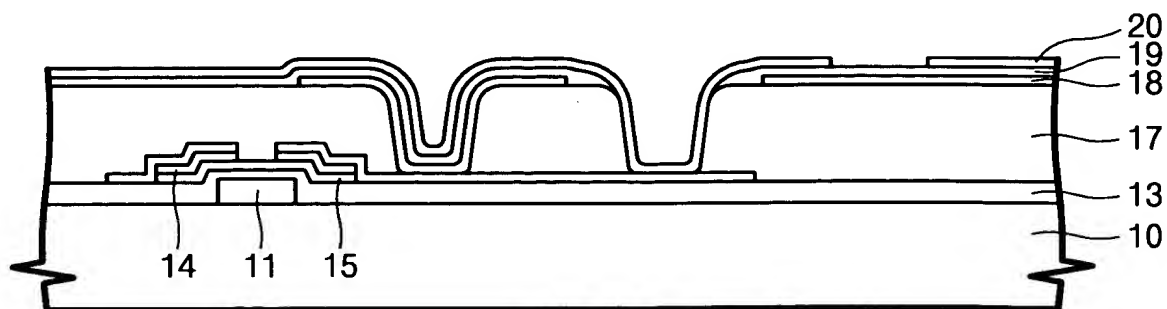
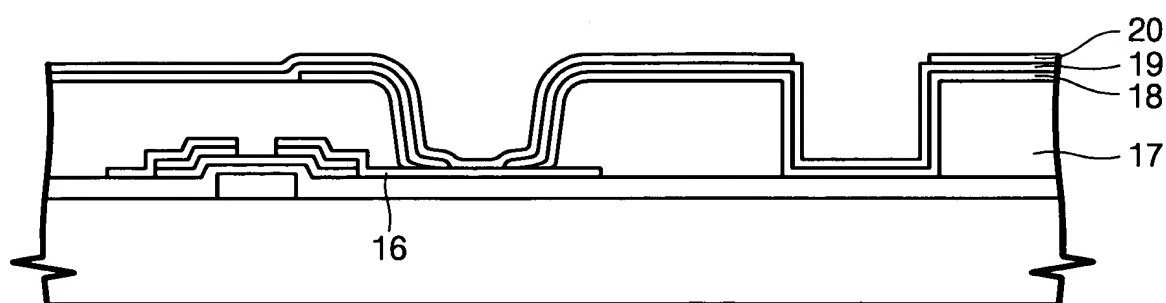


Fig. 12



APPROVED	O.G. FIG. 14A	
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Fig. 14A



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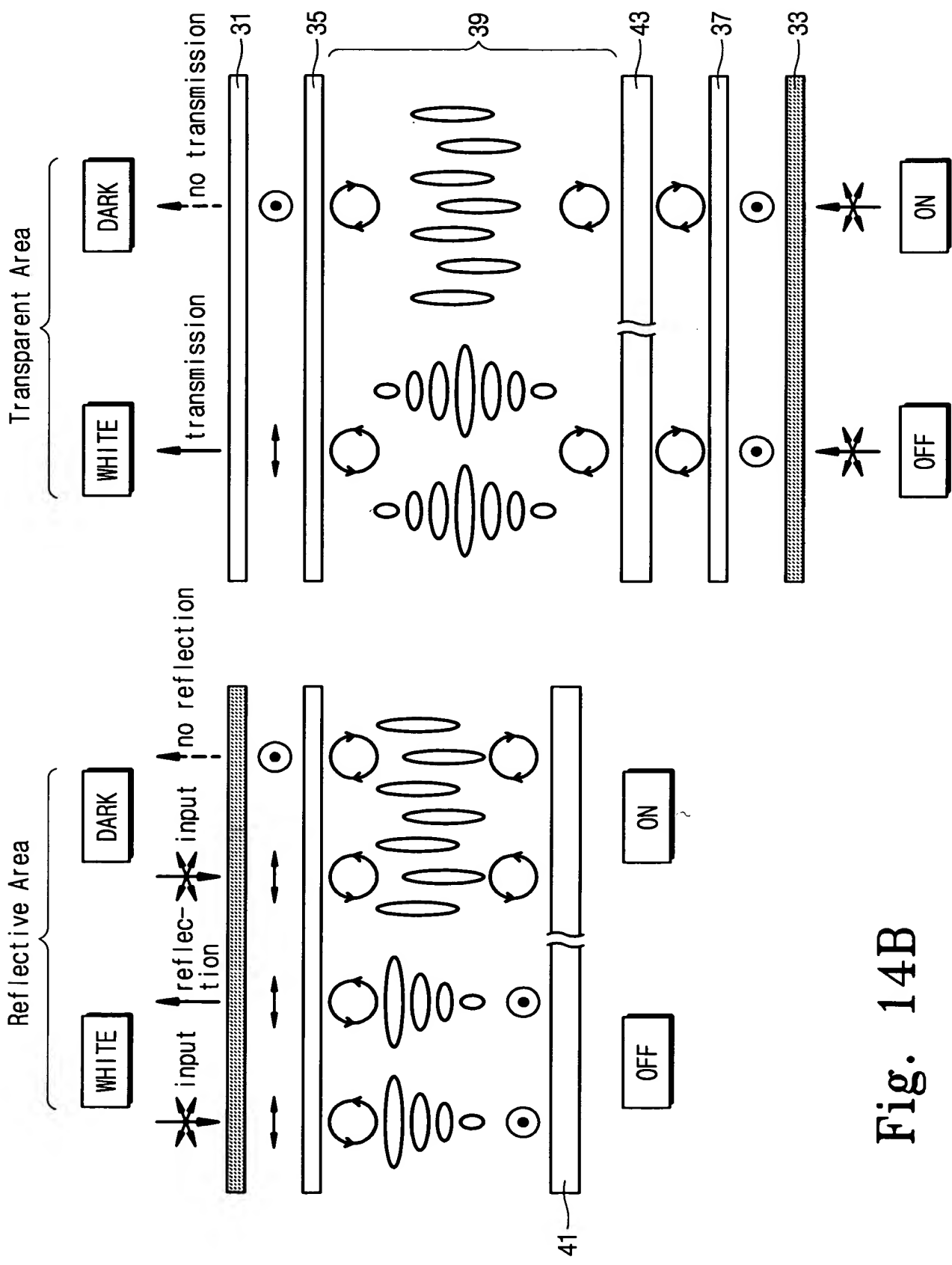


Fig. 14B

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Fig. 15

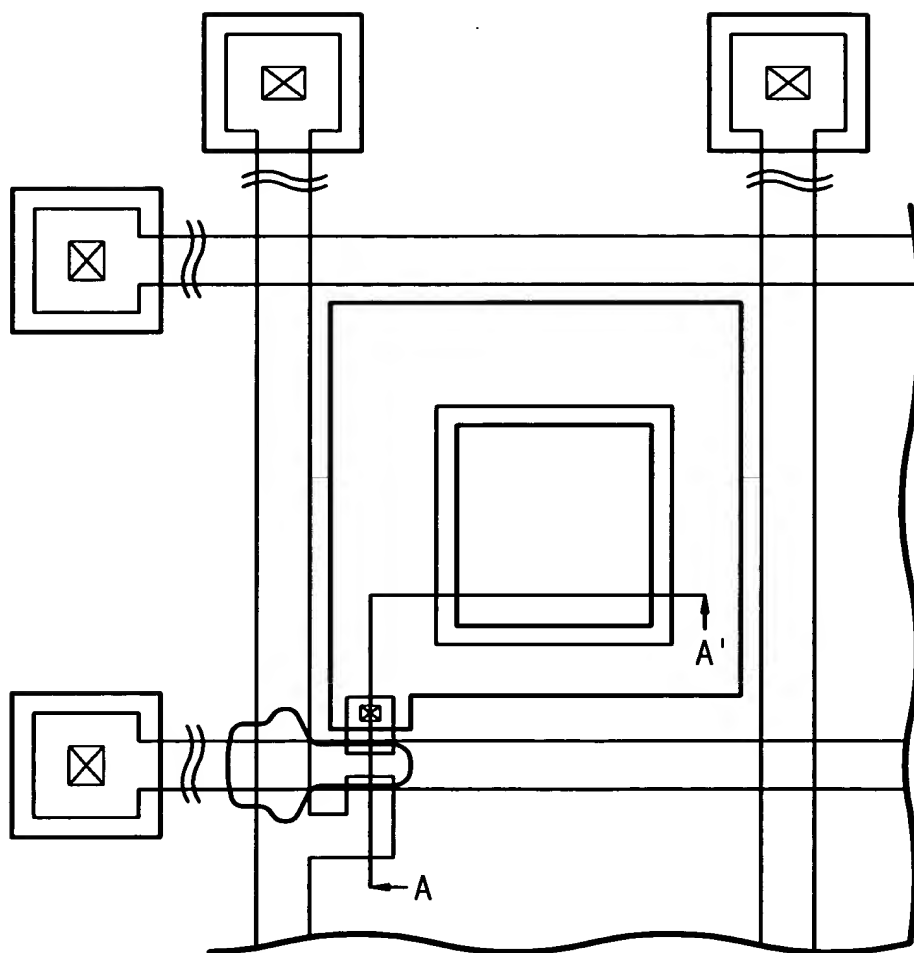


Fig. 16

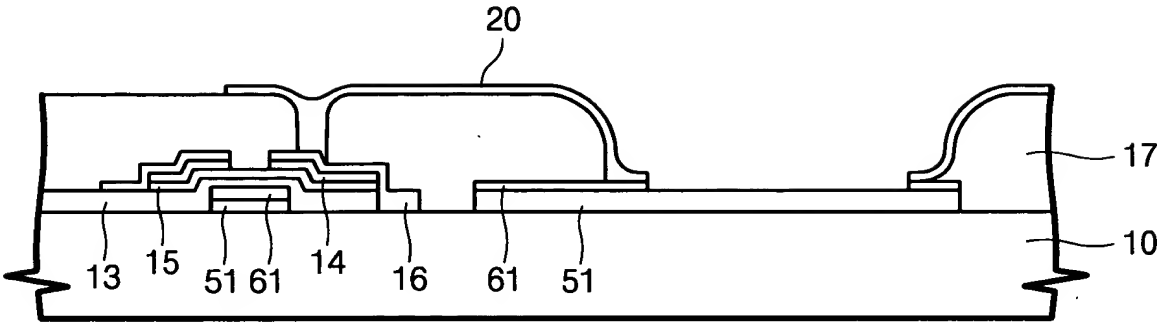


Fig. 17

